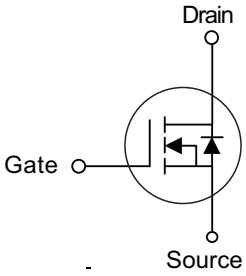
■ PRODUCT CHARACTERISTICS

V_{DSS}	60V
R_{DS} (on)typ(@V_{GS} =10 V)	56mΩ
R_{DS} (on)typ(@V_{GS} =4.5 V)	63mΩ
I_D	7A

Symbol

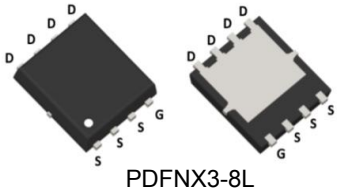


■ APPLICATIONS

- Portable Equipment and Battery Powered systems.
- Power Management in Notebook Computer

■ FEATURES

- Lower $R_{DS(ON)}$ to Minimize Conduction Losses
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested



PDFNX3-8L

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT6568J	PDFN3X3-8L	5000 pieces/Reel

■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C Unless Otherwise Noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current Continuous	I_D	7	A
Drain Current Continuous(Tc=100°C)	I_D(100°C)	5	A
Drain Current Pulsed	I_{DM}	40	A
Power Dissipation	P_D	2.1	W
Junction to Ambient	$R_{\theta JA}$	60	°C/W
Junction Temperature	T_J	+150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

■ ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Off characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	60	69	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0	1.4	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5A	-	56	60	mΩ
		V_{GS}=4.5V, I_D=4A	-	63	70	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=7A	5	-	-	S
Dynamic characteristics						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	1920	-	PF
Output Capacitance	C_{oss}		-	155	-	PF
Reverse Transfer Capacitance	C_{rss}		-	116	-	PF
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	V_{DS}=30V, R_L=4.7Ω V_{GS}=10V,R_{GEN}=3Ω	-	8	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	nS
Turn-Off Fall Time	t_f		-	6	-	nS
Total Gate Charge	Q_g	V_{DS}=30V,I_D=7A, V_{GS}=10V	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	8	-	nC
Gate-Drain Charge	Q_{gd}		-	16	-	nC
Drain-source diode characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=7A	-	-	1.2	V
Diode Forward Current	I_S		-	-	7	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, I_F =7A di/dt = 100A/μs	-	35	-	nS
Reverse Recovery Charge	Qrr		-	43	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

■ TYPICAL CHARACTERISTICS

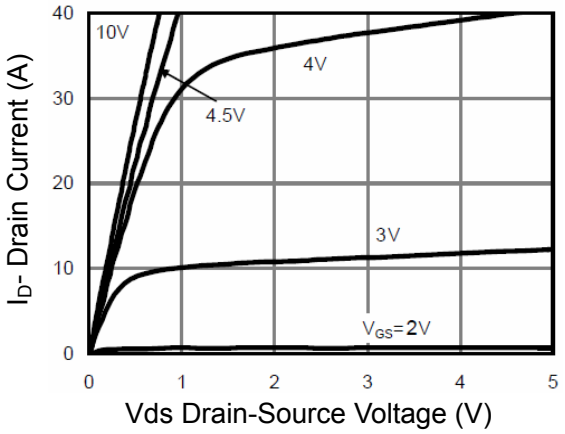


Figure 1 Output characteristics

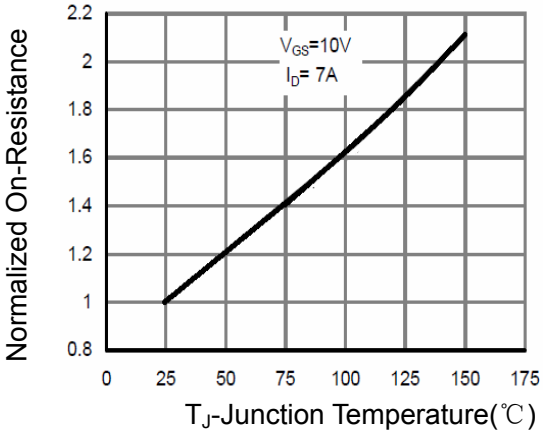


Figure 2 Rdson-junction temperature

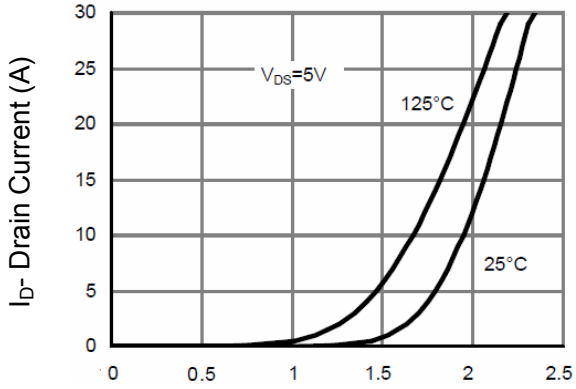


Figure 3 Transfer characteristics

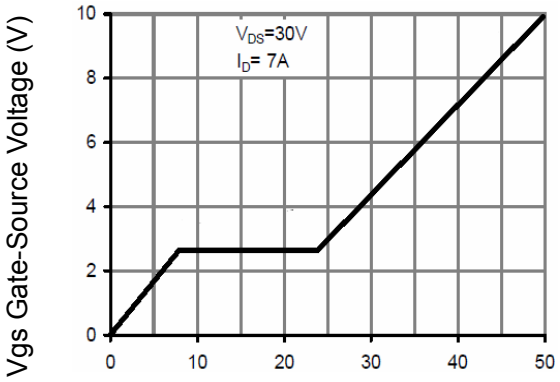


Figure 4 Gate charge

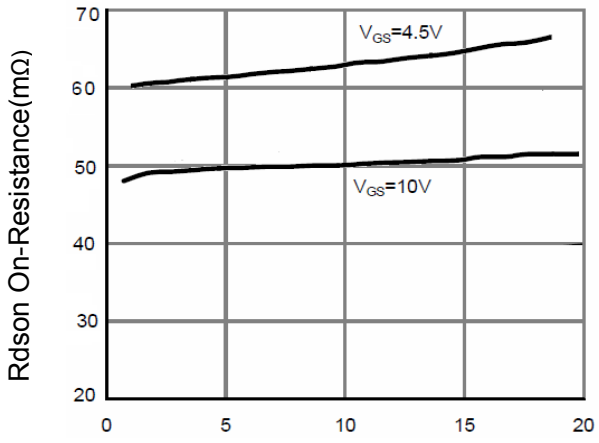


Figure 5 Rdson-drain current

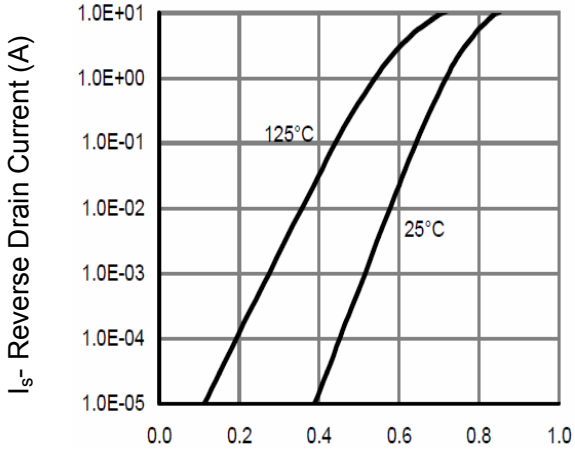


Figure 6 Source-drain diode forward

■ TYPICAL CHARACTERISTICS(Cont.)

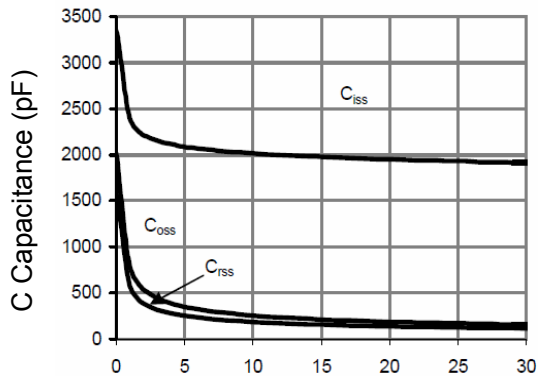


Figure 7 Capacitance vs vds

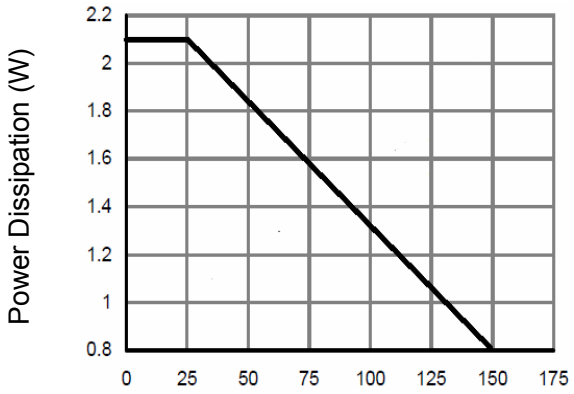


Figure 8 Power de-rating

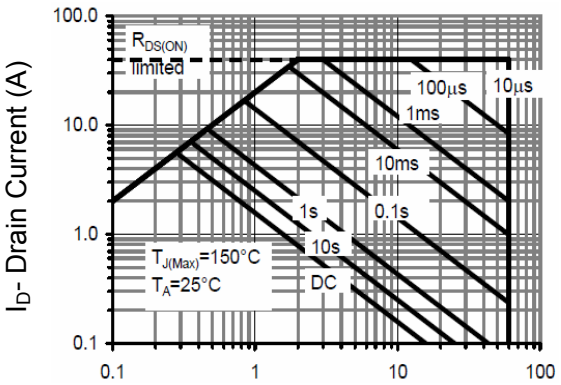


Figure 9 Safe operation area

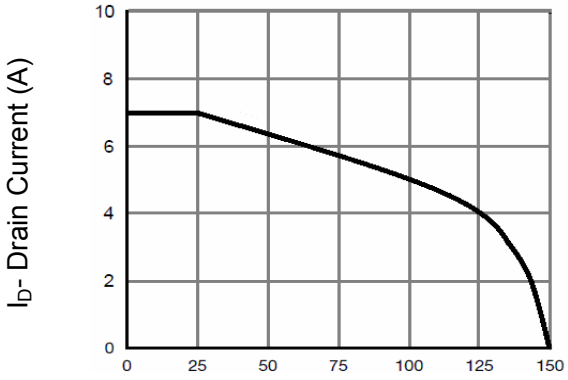


Figure 10 Current de-rating

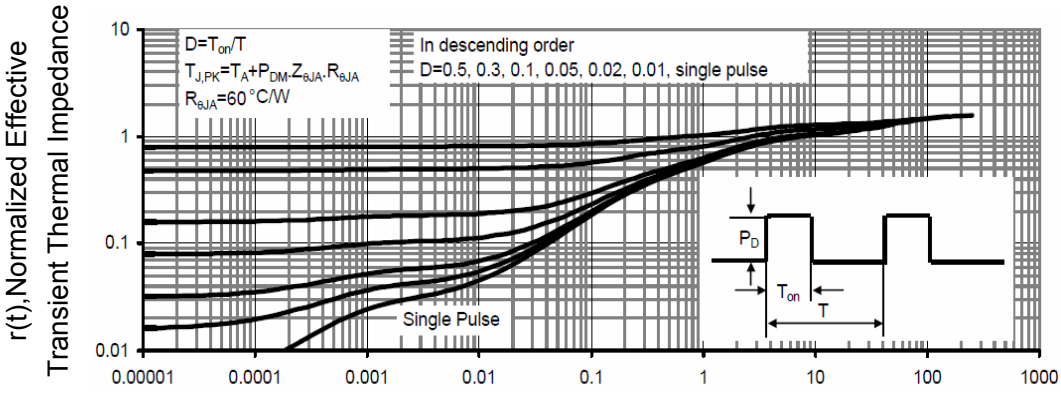
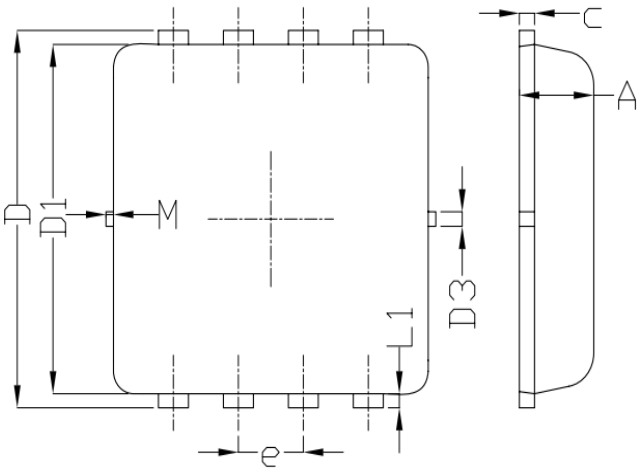
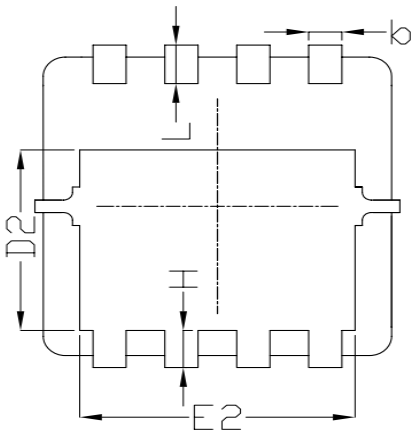
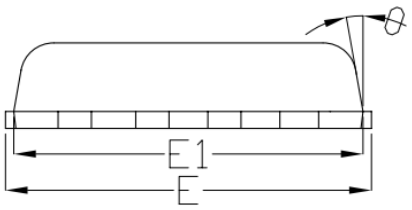


Figure 11 Noemalized maximum transient thermal impedance

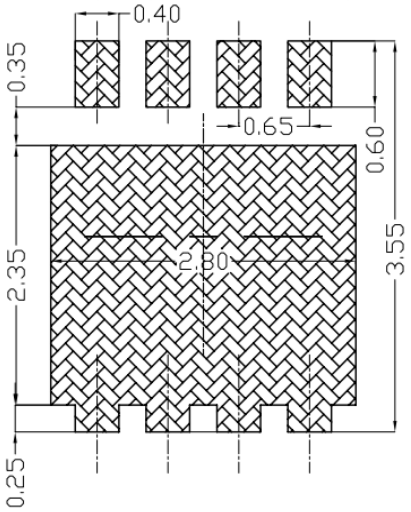
■ PDFN3X3-8L Package Mechanical Data







Land Pattern
(Only for Reference)



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			